

FORMING METHOD OF RESIST PATTERN AND FORMING METHOD OF ANTIREFLECTION FILM

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Abstract of JP8078322

PURPOSE: To provide a stable forming method of a resist pattern and a new forming method of an antireflection film excellently even at the time of the fine resist pattern.

CONSTITUTION: An antireflection film ARL composed of a silicon oxide film (SiO_xNy or SiO_xNyHz) containing at least nitrogen is formed onto a foundation substrate S directly or through another layer. A photo-resist PR is formed onto the antireflection film ARL directly or through another layer. The photo-resist PR is exposed, and a mask pattern is transferred. It is favorable that an antireflection film having a reflection refractive index (n) from 1.2 to 3.4 in an exposure wavelength of 150-450nm, an absorption refractive index (k) from 0.16 to 0.72 and film thickness from 10nm to 100nm is formed as the antireflection film.

